

NPN SILICON TRANSISTOR 2SC2408

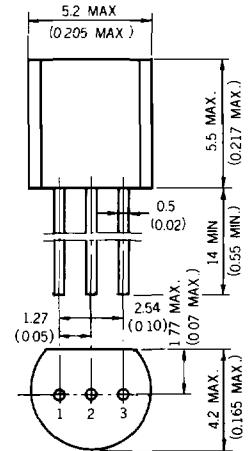
DESCRIPTION 2SC2408 is designed for High frequency Wide Band Amplifier.

- FEATURES**
- $|S_{21e}|^2$: 21 dB TYP. @200 MHz
 - NF : 2.4 dB TYP. @200 MHz

ABSOLUTE MAXIMUM RATINGS

- Maximum Temperatures
- Storage Temperature -65 to +150 °C
 - Junction Temperature +150 °C Maximum
- Maximum Power Dissipation (Ta=25 °C)
- Total Power Dissipation 600 mW
- Maximum Voltages and Current (Ta=25 °C)
- V_{CBO} Collector to Base Voltage 35 V
 - V_{CEO} Collector to Emitter Voltage 18 V
 - V_{EBO} Emitter to Base Voltage 3.0 V
 - I_C Collector Current 150 mA

PACKAGE DIMENSIONS
in millimeters (inches)

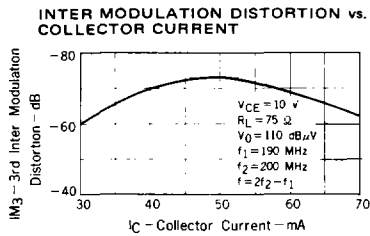
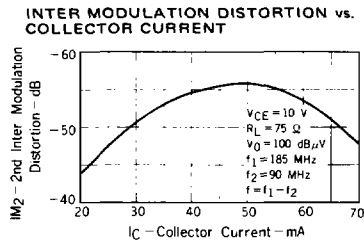
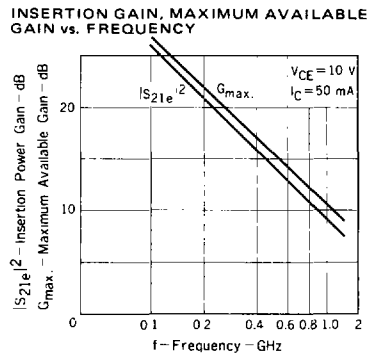
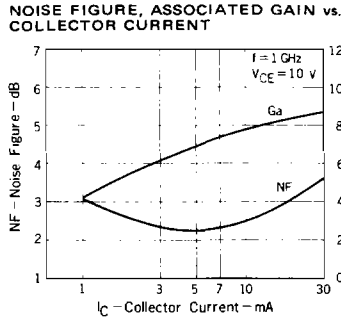
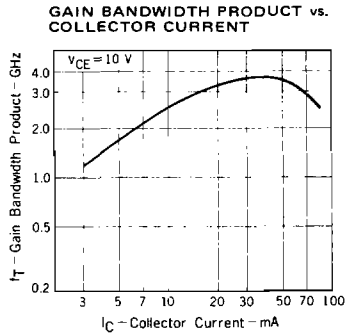
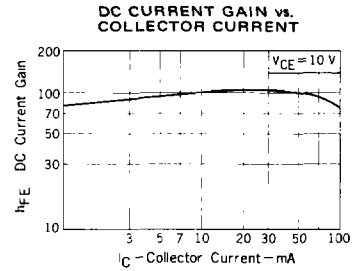
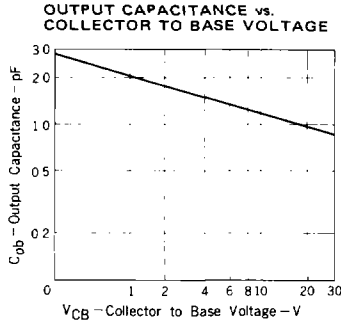
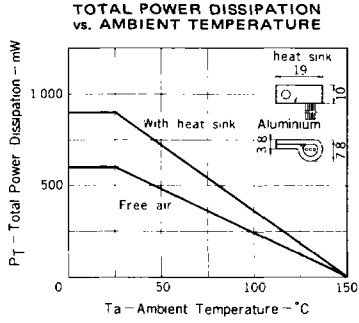


- 1. BASE EIAJ : SC-43
- 2. EMITTER JEDEC : TO-92
- 3. COLLECTOR IEC : PA33

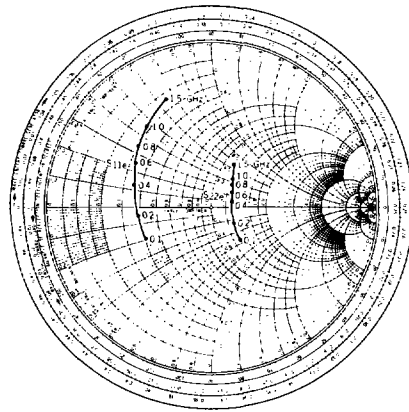
ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
h _{FE}	DC Current Gain	30	100	200		V _{CE} =10 V, I _C =50 mA
f _T	Gain Bandwidth Product		3.5		GHz	V _{CE} =10 V, I _C =50 mA
C _{ob}	Output Capacitance		1.25	2.0	pF	V _{CB} =10 V, I _E =0, f=200 MHz
S _{21e} ²	Insertion Power Gain	18	21		dB	V _{CE} =10 V, I _C =50 mA, f=200 MHz, R _G =50 Ω
NF	Noise Figure		2.4	4.0	dB	V _{CE} =10 V, I _C =30 mA, f=200 MHz, R _G =50 Ω
I _{CBO}	Collector Cutoff Current			0.5	μA	V _{CB} =20 V, I _E =0
I _{EBO}	Emitter Cutoff Current			0.5	μA	V _{EB} =2.0 V, I _C =0

TYPICAL CHARACTERISTICS (Ta=25 °C)



TYPICAL "S" PARAMETER



V_{CE} = 10 V
I_C = 50 mA
Z₀ = 50 Ω

